

PROCEEDINGS OF SPIE

High-Power Diode Laser Technology and Applications X

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Editor

22–24 January 2012
San Francisco, California, United States

Sponsored and Published by
SPIE

Volume 8241

Proceedings of SPIE, 0277-786X, v. 8241

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Please use the following format to cite material from this book:

Author(s), "Title of Paper," in *High-Power Diode Laser Technology and Applications X*, edited by Mark S. Zediker, Proceedings of SPIE Vol. 8241 (SPIE, Bellingham, WA, 2012) Article CID Number.

ISSN 0277-786X
ISBN 9780819488848

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
SPIE.org

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Introduction

This is the tenth year of the High-Power Diode Laser Technology and Applications Conference. When this conference started, the state of the art laser diode produced 50 watts with a 45-50% efficiency. Over the years, there was a steady increase in both the power and the efficiency of these devices and this year, 200-watt bars were the standard with >70% efficiency. This conference has played a pivotal role in this evolution, allowing the authors to share their results and compete with each other in a very open environment. This year, we also saw papers on breakthrough performance in laser diode system brightness and power. With laser diode systems matching the brightness of conventional lasers systems, the next ten years promise to be interesting, as these systems evolve and continue to achieve breakthrough efficiency and performance. I look forward to the next ten years because of the bright future for direct diode laser systems.

Mark S. Zediker

